



NXH160T120L2Q1

(PIM)IGBT 1200 V160 A 650 V100 A

NXH160T120L2Q1 (PIM) T 160A / 1200V IGBT100A / 1200V 100A / 650V IGBT 100A / 650V (NTC)

- 1200V IGBT Specifications: VCE(SAT) = 2.1V @ 160A, ESW = 6.3mJ @ 100A
- 650V IGBT Specifications: VCE(SAT) = 1.65V @ 150A, ESW = 3.8mJ @ 100A
- Thermistor
- 150A rated half bridge diodes
- Fast switching IGBT with low VCE(SAT) for high efficiency
- Fast switching IGBT with low VCE(SAT) for high efficiency
- Temperature detection
- Supports reactive power flow
- Solar Inverter DC-AC stage
- UPS DC-AC stage
- Battery Storage DC-AC stage
- Solar Inverter
- UPS
- Battery Storage

	Pricing (\$/Unit)	Compliance	Status	Configuration	V _{BR} Max (V)	Rated Current (A)	V _{CE(sat)} Typ (V)	V _F Typ (V)	Application	Package Type
NXH160T120L2Q1SG	72.4062	 	Active	Split T-Type Inverter	1200	160	2.1	2.2	Industrial	Q1